

<p style="text-align: center;">O P E R A T I O N INFORMATION DISCLOSURE CITATION JAN 09 2002 <i>(use several sheets if necessary)</i></p>	Docket Number (Optional) <b>2898.2US (88-070.7)</b>	
	Application Number <b>09/776,387</b>	
	Applicant <b>Protigal et al.</b>	
	Filing Date <b>February 2, 2001</b>	Group Art Unit <b>2826</b>

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
X	3,699,722	10/1 972	Davidson et al.			
	4,061,999	12/1977	Proebsting et al.			
	4,271,461	06/1981	Hoffmann et al.			
	4,346,459	08/1982	Sud et al.			
	4,389,715	06/1983	Eaton, Jr. et al.			
	4,458,336	07/1984	Takemae			
	4,494,221	01/1985	Hardee et al.			
	4,566,081	01/1986	Ochii			
	4,587,639	05/1986	Aoyama et al.			
	4,628,214	12/1986	Leuschner			
	4,631,421	12/1986	Inoue et al.			
X	4,658,379	04/1987	Fujishima et al.			

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
A.S.	56-148859	11/1981	Japan			X	
	56-153778	11/1981	Japan			X	
	57-001902	01/1982	Japan			X	
	01-268032	10/1989	Japan			X (only)	

**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)

A.S.	McKennay, Verron D., "Good bits swapped for bad in 64-kilobit E-PROM," pps. 115-120 plus Cover and Table of Contents, <u>Electronics</u> , March 13, 1990.
A.S.	Natori et al., "FAM: 16.5: A 34ns 256K DRAM," pps. 232-233 plus Cover and Table of Contents, <u>IEEE International Solid-State Circuits Conference</u> , February 25, 1983.
	<u>Research Disclosure</u> , (3 pages), June 1985.

EXAMINER

AS

DATE CONSIDERED

11-29-02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449 O P E J C INFORMATION DISCLOSURE CITATION JAN 09 2002 U.S. PATENT & TRADEMARK OFFICE (use several sheets if necessary)		Docket Number (Optional) <b>2898.2US (88-070.7)</b>	Application Number <b>09/776,387</b>				
		Applicant <b>Protigal et al.</b>					
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<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
A.S.	4,716,549	12/1987	Nakano et al.				
	4,730,276	03/1988	Waller				
	4,780,850	10/1988	Miyamoto et al.				
	4,780,851	10/1988	Kurakami				
	4,780,852	10/1988	Kajigaya et al.				
	4,829,480	05/1989	Seo				
	4,930,112	05/1990	Tanaka et al.				
	4,943,960	07/1990	Komatsu et al.				
	4,987,325	01/1991	Seo				
	5,012,132	04/1991	Wang				
	5,038,325	08/1991	Douglas et al.				
	5,042,011	08/1991	Casper et al.				
<b>FOREIGN PATENT DOCUMENTS</b>							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
<b>OTHER DOCUMENTS</b>				(Including Author, Title, Date, Pertinent Pages, Etc.)			
A.S.		"Decoupling Capacitor Structure to Reduce FET Output Driver Switching Noise," pps. 167-168, <u>IBM Technical Disclosure Bulletin</u> , Vol 30., No. 7, December 1987.					
A.S.		"MOS Memory," (4 pages), <u>Toshiba Mos Memory Products Data Book</u> , April 1987.					
A.S.		"Double-Traversing Pseudo-Folded-Bitline Design for Cross-Point Memory Cells," pps. 246-248, <u>IBM Technical Disclosure Bulletin</u> , Vol. 30, No. 11, April 1988.					
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<b>U.S. PATENT DOCUMENTS</b>					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
<i>A.S.</i>	5,177,908	01/1993	Tuttle		
	RE 34,425	11/1993	Schultz		
	5,315,551	05/1994	Hirayama		
	5,345,110	09/1994	Renfro et al.		
	RE 35,825	06/1998	Zager		
<b>FOREIGN PATENT DOCUMENTS</b>					
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
					YES
<b>OTHER DOCUMENTS</b> (Including Author, Title, Date, Pertinent Pages, Etc.)					
<i>A.S.</i>		"New Memory Products 1987/1988," (4 pages), <u>NEC Electronics Inc. Supplement to 1986 Memory Products Data Book</u> , December 1987.			
<i>A.S.</i>		Gillingham et al., "High-Speed, High-Reliability Circuit Design for Megabit DRAM," pps. 1171-1175 plus Table of Contents, <u>IEEE Journal of Solid-State Circuits</u> , Vol 26, No. 8, August 1991.			
<i>A.S.</i>		"IBM's Response to Micron," (22 pages), December 8, 1995.			
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